

Rev.A May.-2023

TO-220 N

N-CHANNEL MOSFET in a TO-220 Plastic Package.

$V_{DS}=40V$ $I_D=177A$ $V_{GS}=\pm 20V$

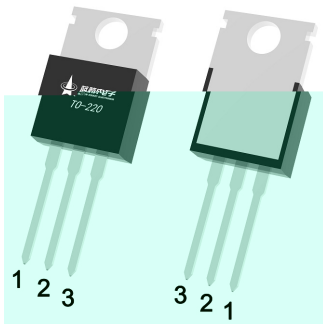
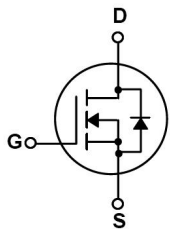
$R_{DS(on)}@10V$ 3.0m (Type.2.5m)

$R_{DS(on)}@4.5V$ 5.0m (Type.3.5m)

HF Product.

DC/DC

DC Motor Driver,Synchronous Rectification in DC/DC Converters.



PIN1 G

PIN 2 4 D

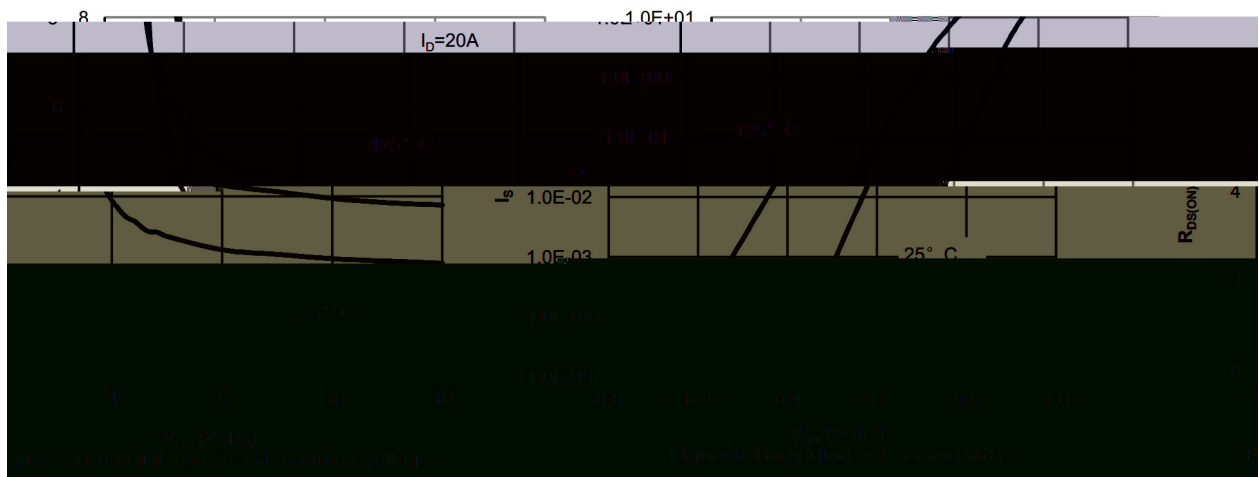
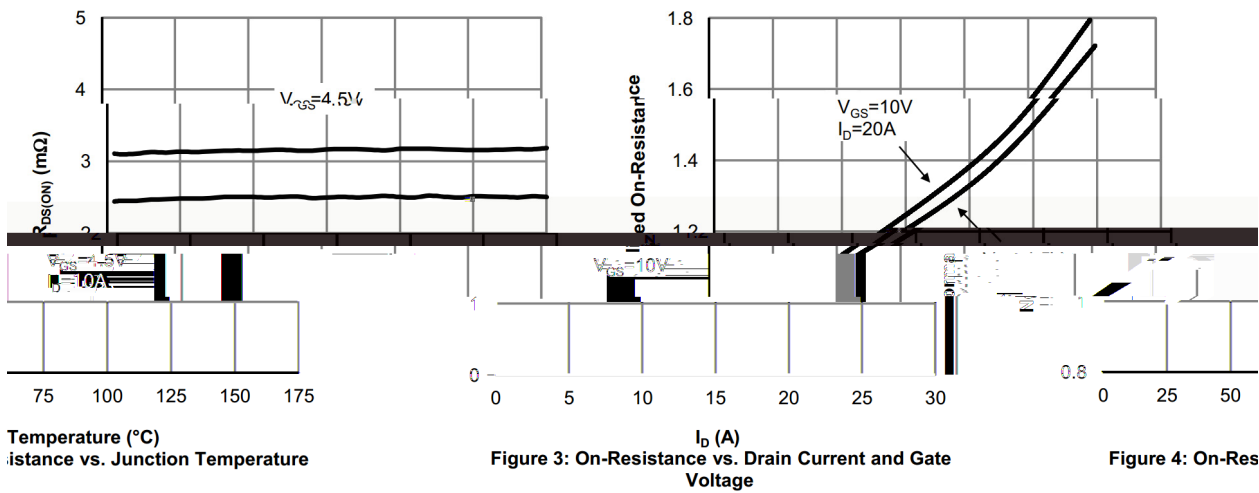
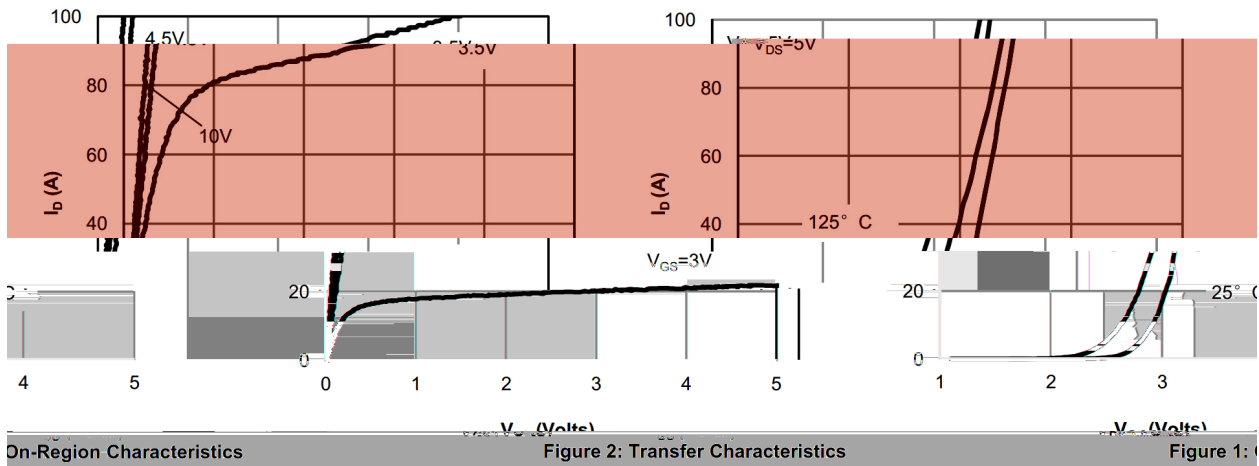
PIN 3 S

See Marking Instructions.

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	40	V
Drain Current		$I_D(T_c=25^\circ\text{C})$	177	A
Pulsed Drain Current		I_{DM}	560	A
Gate-Source Voltage		V_{GS}	± 20	V
Single Pulsed Avalanche Energy $L=0.5\text{mH}$		E_{AS}	435	mJ
Avalanche Current		I_{AS}	33	A
Total Power Dissipation		$P_D(T_c=25^\circ\text{C})$	170	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	
Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	15	/W
	Steady-State		60	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	0.74	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0\text{V}$ $I_D=250\text{A}$	40	47		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40\text{V}$ $V_{GS}=0\text{V}$			1	A
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20\text{V}$ $V_{DS}=0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\text{A}$	1	1.7	3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$ $I_D=20\text{A}$		2.5	3	m
		$V_{GS}=4.5\text{V}$ $I_D=10\text{A}$		3.5	5	
Forward On Voltage	V_{SD}	$V_{GS}=0\text{V}$ $I_S=1\text{A}$			1.2	V
Gate resistance	R_g	$V_{GS}=0\text{V}$ $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.3		
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}$ $V_{GS}=0\text{V}$ $f=1\text{MHz}$		9600		pF
Output Capacitance	C_{oss}			740		
Reverse Transfer Capacitance	C_{rss}			650		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10\text{V}$, $I_D=20\text{A}$ $V_{DS}=20\text{V}$		51		nC
Total Gate Charge	$Q_{g(4.5V)}$			23		
Gate Source Charge	Q_{gs}			13.2		
Gate Drain Charge	Q_{gd}			3.1		

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=20V$ $R_L=1\Omega$ $R_{GEN}=3\Omega$		11		ns
Turn-On Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(off)}$			40		
Turn-Off Fall Time	t_f			10		



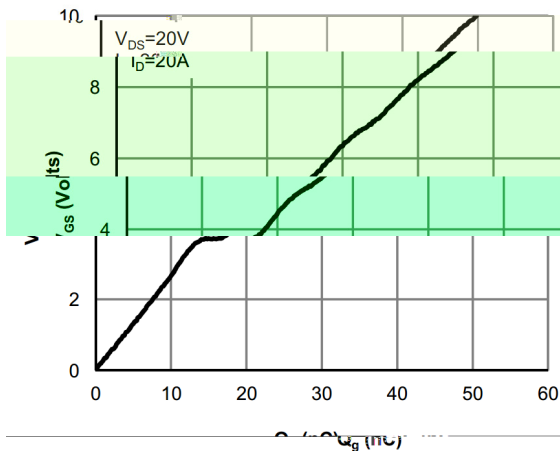


Figure 7: Gate-Charge Characteristics

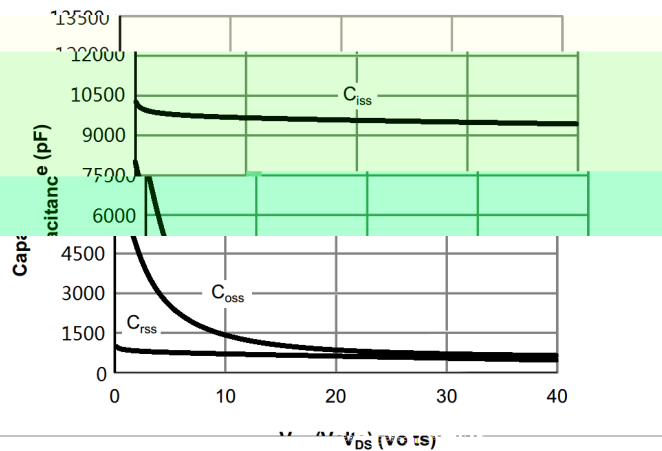


Figure 8: Capacitance Characteristics

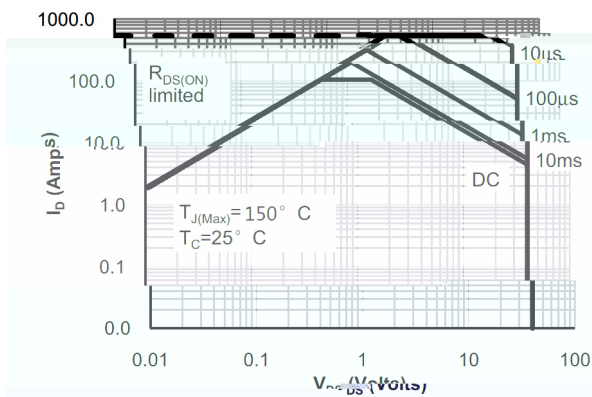


Figure 9: Maximum Forward Biased Safe Operating Area

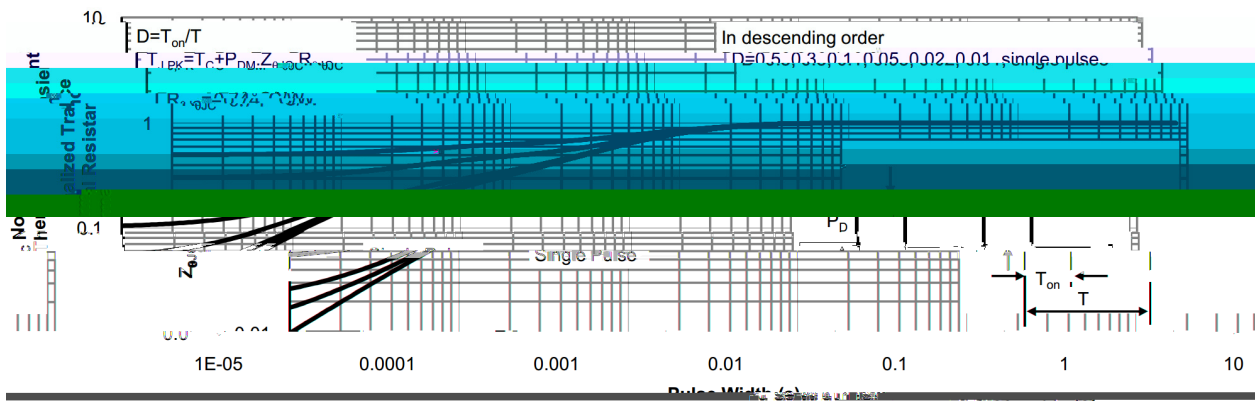
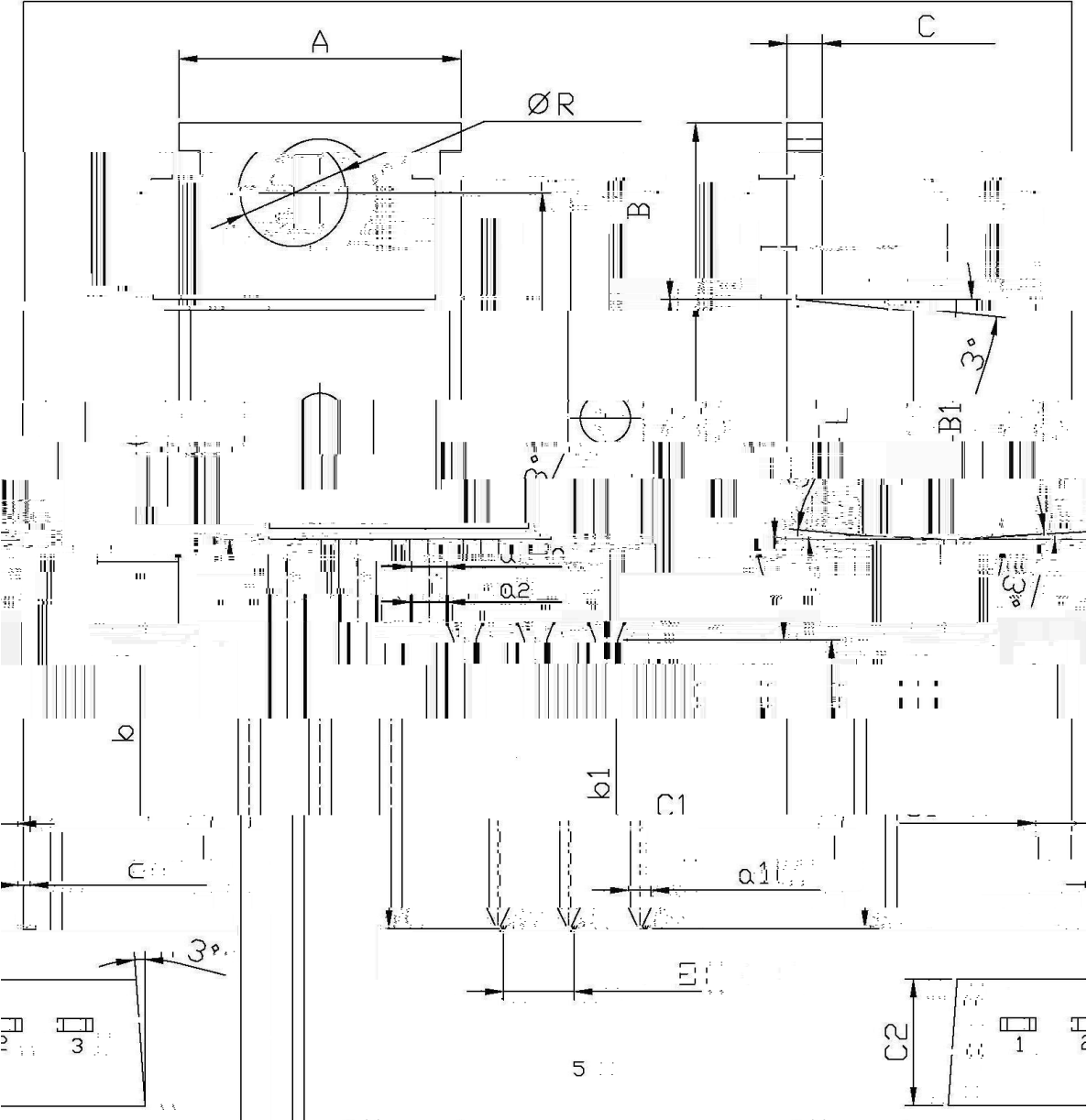


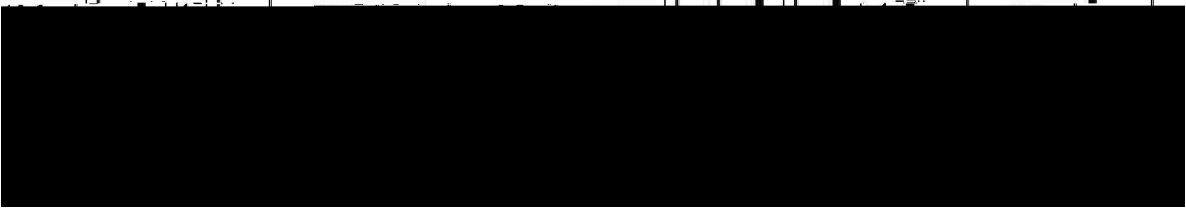
Figure 10: Normalized Maximum Transient Thermal Impedance

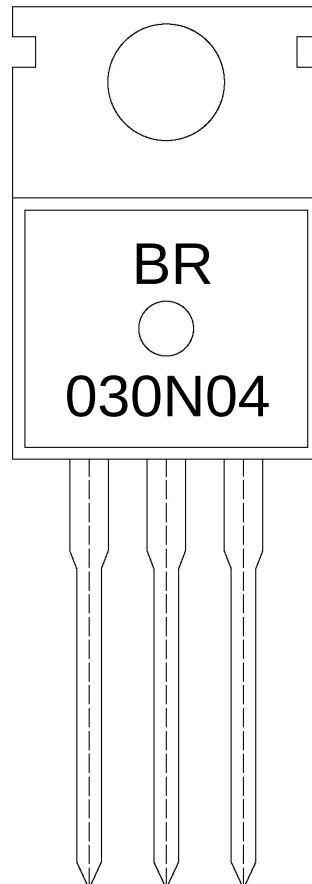
T□-220

单位：mm



Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min	Max	Symbol	Min	Max
C	1.2	1.4	A	9.8	10.2
B	6.3	6.7	R	3.56	3.64
B1	9.0	9.4	L	15.7	16.1
C1	2.2	2.6	b	12.6	13.6





BR

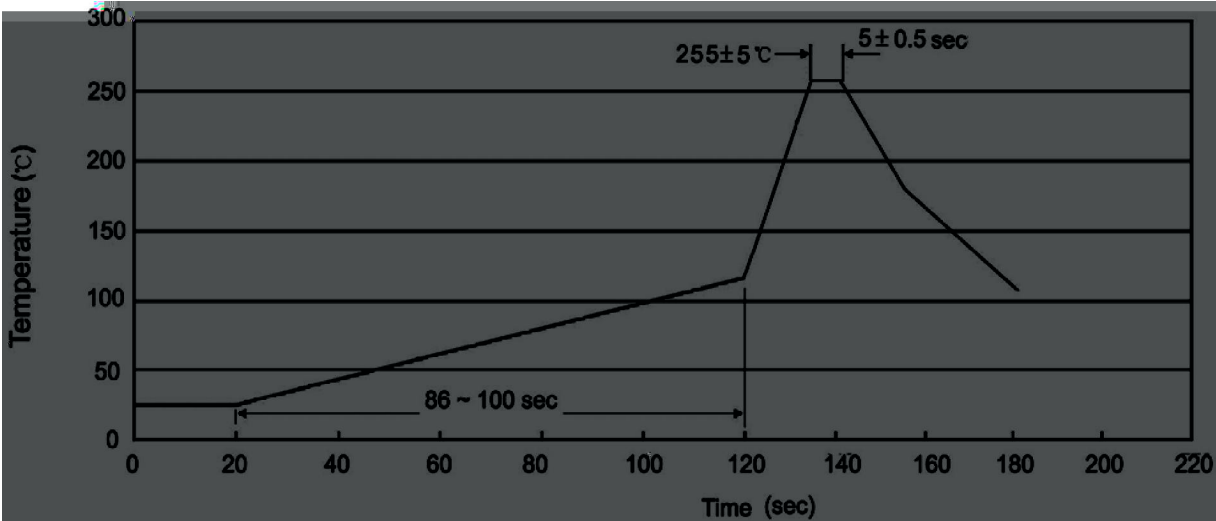
030N04

Note:

BR: Company Code

030N04: Product Type

****: Lot No. Code, code change with Lot No



- Note:

1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10 /sec.
- 1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units					Dimension (unit mm ³)		
	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195